L Number	Hits	Search Text	DB	Time stamp
25	40	(high adj density adj plasma or HDP) near10 improv\$ same (deposit\$ and etch\$)	USPAT; US-PGPUB; EPO; JPO;	2003/11/17 09:35
-	23	US-4960488-\$.DID. OR US-5279865-\$.DID. OR US-5302233-\$.DID. OR US-5362526-\$.DID. OR US-0416048-\$.DID. OR US-5599740-\$.DID. OR US-0850105-\$.DID. OR US-0872052-\$.DID. OR US-6030881-\$.DID. OR US-6170428-\$.DID. OR	EPO; JPO;	2003/11/14 10:58
-	22	US-6182602-\$.DID. OR US-6189483-\$.DID. dep\$1etch\$1dep	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:18
	0	depost\$4 near3 etch\$4 near4 deposit\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:18
_	0	depost\$1etch\$4deposition	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:18
_	9	deposition\$1etching\$1deposition	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:20
-	15100	plasma near10 deposit\$4 and plasma near10 etch\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:20
_	53580	plasma near10 deposit\$4 sameplasma near10 etch\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:20
	9197	plasma near10 deposit\$4 same plasma near10 etch\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:20
_	6037	plasma near5 deposit\$4 same plasma near5 etch\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30
_	115	plasma near5 deposit\$4 same plasma near5 etch\$4 same in\$1situ	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30
_	26	(plasma near5 deposit\$4 same plasma near5 etch\$4 same in\$1situ) same (silicon)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/09/30 14:21
_	16	continuous near10 in\$1situ same etch\$4	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 14:59

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_	15	continuous near10 in\$1situ same plasma	USPAT;	2003/09/30
			US-PGPUB;	15:52
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	15	overlap\$5 near5 flow\$4 same plasma	USPAT;	2003/09/30
	-	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	US-PGPUB;	16:03
			EPO; JPO;	1 20:00
			DERWENT;	
				ļ
1_	8604	denogité de nounio etabé de nounio el anua	IBM_TDB	0000/00/00
	1 0004	deposit\$4 near10 etch\$4 near10 plasma	USPAT;	2003/09/30
	•		US-PGPUB;	16:04
		i	EPO; JPO;	
			DERWENT;	[
			IBM_TDB	i
-	144	The state of the s	USPAT;	2003/09/30
	1	same in\$1situ	US-PGPUB;	16:04
			EPO; JPO;	
			DERWENT;	1
			IBM TDB	1
-	9	deposit\$4 near10 etch\$4 near10 plasma	USPAT;	2003/09/30
	1	same in\$1situ same (overlap\$5 or	US-PGPUB;	16:37
	1	continu\$5)	EPO; JPO;	
			DERWENT;	
	i		IBM TDB	
	21	PECVD same (silicon adj dioxide or	_	
	""	silicon adi mitmidal sama (samuala)	USPAT;	2003/09/30
]	silicon adj nitride) same (fluoride)	US-PGPUB;	16:40
	İ		EPO; JPO;	
			DERWENT;	1
			IBM_TDB	ļ I
1 -	670	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPAT;	2003/09/30
		silicon adj nitride) same silane	US-PGPUB;	16:40
			EPO; JPO;	
			DERWENT;]
			IBM TDB	1
-	275	PECVD same (silicon adj dioxide or	USPAT;	2003/09/30
		silicon adj nitride) near10 silane	US-PGPUB;	16:40
İ		land the state of	EPO; JPO;	10.40
			DERWENT;	
_	0	PECVD same (silicon adj dioxide or	IBM_TDB	0000/00/00
İ		giligon add mitmidal manual miles and	USPAT;	2003/09/30
	İ	silicon adj nitride) near10 silane near10	US-PGPUB;	16:40
		fluorine	EPO; JPO;	
1] .		DERWENT;	
	1	DROVE (13.4)	IBM_TDB	1
I -	38	PECVD same (silicon adj dioxide or	USPAT;	2003/09/30
		silicon adj nitride) near10 fluorine	US-PGPUB;	17:08
			EPO; JPO;	[
	!		DERWENT;	
1	ļ l		IBM TDB	1
-	11	poloidal near4 ion	USPAT;	2003/09/30
1			US-PGPUB;	17:11
]] [EPO; JPO;	
1	1		DERWENT;	
	1			ļ
l -	8	"1158565"	IBM_TDB USPAT;	2002/00/20
[2003/09/30
	1		US-PGPUB;	17:11
	1		EPO; JPO;	
			DERWENT;	
_	300	3m01 = 3m1 = 1 = 1 = 1 = 1	IBM_TDB	
-	722	in\$1situ near3 etch\$	USPAT;	2003/11/13
	1		US-PGPUB;	11:26
	j ł		EPO; JPO;	
		i	DERWENT;	
	1		IBM TDB	
· -	1	in\$1situ near3 etch\$ and toroidal near3	USPAT;	2003/11/13
		plasma	US-PGPUB;	11:27
]			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	·		TDEI IND	

				
-	83	etch\$ and toroidal near3 plasma	USPAT;	2003/11/13
	İ		US-PGPUB;	11:27
			EPO; JPO;	
			DERWENT; IBM TDB	
_	9	etch\$ and toroidal near3 plasma same	USPAT;	2003/11/13
		parallel	US-PGPUB;	11:35
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	8	toroidal near3 plasma and cox.in.	USPAT;	2003/11/13
			US-PGPUB;	11:33
İ			EPO; JPO;	
			DERWENT;	
	68	toroidal near3 plasma same parallel	IBM_TDB	2002/11/12
		coroldal hears plasma same parallel	USPAT;	2003/11/13
			US-PGPUB; EPO; JPO;	11:36
			DERWENT;	
			IBM TDB	
_	49	toroidal near3 plasma same parallel and	USPAT;	2003/11/13
		poloidal	US-PGPUB;	11:36
			EPO; JPO;	İ
			DERWENT;	
			IBM_TDB	
_	25	The second second persons and persons bounds	USPAT;	2003/11/13
i		poloidal	US-PGPUB;	11:42
			EPO; JPO;	1
			DERWENT;	i i
_	85	parallel same poloidal	IBM_TDB USPAT;	2002/11/12
		Paraffer Same Porotdar	US-PGPUB;	2003/11/13 11:42
			EPO; JPO;	11.42
			DERWENT;	
			IBM TDB	
] -	6	(parallel same poloidal) and etch\$	USPAT;	2003/11/13
			US-PGPUB;	11:49
			EPO; JPO;	
			DERWENT;	
_	7	maladal masu2 day	IBM_TDB	2000 (44 (40
	/	poloidal near3 ion	USPAT; US-PGPUB;	2003/11/13
			EPO; JPO;	11:49
			DERWENT;	
			IBM TDB	
-	4169	continuous\$ near4 plasma	USPAT;	2003/11/14
			US-PGPUB;	10:58
	1		EPO; JPO;	
	[DERWENT;	
_	470	gentinuouse massia silvisia	IBM_TDB	0000 (000 (000
[-	472	continuous\$ near4 plasma same etch\$	USPAT;	2003/11/14
			US-PGPUB;	10:58
Į į			EPO; JPO; DERWENT;	
			IBM TDB	
-	110	continuous\$ near4 plasma same etch\$ same	USPAT;	2003/11/14
]	(dep or deposit\$)	US-PGPUB;	11:32
			EPO; JPO;	
<u> </u>			DERWENT;	
			IBM_TDB	
_	10	"dep/etch/dep"	USPAT;	2003/11/14
ļ			US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
_	13013	deposit\$ near2 etch\$ near3 deposit\$	IBM_TDB USPAT;	2003/11/14
	10010	and mark occurs means debosites	US-PGPUB;	11:33
			EPO; JPO;	11.33
	}		DERWENT;	İ
			IBM TDB	I
			·	

				10000/44//4
	3219	_ ·	USPAT;	2003/11/14
		plasma	US-PGPUB; EPO; JPO;	11:33
			DERWENT;	
		•	IBM TDB	
_	679	deposit\$ near2 etch\$ near3 deposit\$ same	USPAT;	2003/11/14
-	0,3	plasma same silicon	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	170		USPAT;	2003/11/14
		plasma same silicon adj dioxide	US-PGPUB;	11:33
			EPO; JPO;	
			DERWENT; IBM TDB	
	71	deposit\$ near2 etch\$ near3 deposit\$	USPAT;	2003/11/14
	'-	near10 plasma same silicon adj dioxide	US-PGPUB;	11:48
	!		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	32		USPAT;	2003/11/14
!		near10 plasma same silicon adj dioxide	US-PGPUB;	13:39
			EPO; JPO; DERWENT;	1
1	-		IBM TDB	
1_	61	dep\$3etch\$3dep\$2 or	USPAT;	2003/11/14
	"	deposit\$4etch\$4deposit\$4	US-PGPUB;	13:17
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	21		USPAT;	2003/11/14
		deposit\$4etch\$4deposit\$4) same plasma	US-PGPUB;	13:22
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	5270264.pn.	USPAT;	2003/11/14
			US-PGPUB;	13:22
			EPO; JPO;	
			DERWENT;	:
			IBM_TDB	2002/11/14
-	110		USPAT; US-PGPUB;	2003/11/14
		near10 plasma	EPO; JPO;	13.39
			DERWENT;	
			IBM TDB	
_	78	(deposit\$ near2 etch\$ near10	USPAT;	2003/11/14
		simultaneous\$ near10 plasma) not	US-PGPUB;	14:11
		(deposit\$ near2 etch\$ near10	EPO; JPO;	
		simultaneous\$ near10 plasma same silicon	DERWENT;	
	1	adj dioxide)	IBM_TDB	2003/11/14
-	13	poloidal near5 ion	USPAT; US-PGPUB;	14:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	411	poloidal same plasma	USPAT;	2003/11/14
			US-PGPUB;	14:14
			EPO; JPO;	
			DERWENT;	
	_	noloidal game places and 420/6 calc	IBM_TDB USPAT;	2003/11/14
-	0	poloidal same plasma and 438/\$.ccls.	US-PGPUB;	14:14
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	20	poloidal near10 parallel same plasma	USPAT;	2003/11/14
			US-PGPUB;	14:19
			EPO; JPO;	
			DERWENT;	
i	1		IBM TDB	

Γ				
-	6	poloidal same plasma and applied.as.	USPAT; US-PGPUB;	2003/11/14 14:19
ŀ			EPO; JPO;	14:19
			DERWENT;	
i			IBM TDB	
-	9	poloidal same plasma and etch\$	USPAT;	2003/11/14
İ	İ		US-PGPUB;	15:03
			EPO; JPO;	
			DERWENT;	
_	2	5252178.pn.	IBM_TDB USPAT;	2003/11/14
		02021/01011	US-PGPUB;	15:10
			EPO; JPO;	10.10
			DERWENT;	
	_		IBM_TDB	
_	2	6167834.pn.	USPAT;	2003/11/14
			US-PGPUB;	15:15
			EPO; JPO;	
			DERWENT;	
_	2	electical near3 bias	USPAT;	2003/11/14
			US-PGPUB;	15:15
			EPO; JPO;	
	1		DERWENT;	
1_	E CO.0	alastnisal manua hida	IBM_TDB	0000/45/55
-	5680	electrical near3 bias	USPAT;	2003/11/14
			US-PGPUB; EPO; JPO;	15:15
			DERWENT;	
			IBM TDB	!
-	85	electrical near3 bias same plasma same RF	USPAT;	2003/11/14
1		•	US-PGPUB;	16:03
			EPO; JPO;	
			DERWENT;	
_	5553918	high enar2 density near3 plasma or HCP	IBM_TDB	2002/11/14
	3333310	might enail density hears plasma of her	USPAT; US-PGPUB;	2003/11/14
			EPO; JPO;	16:03
			DERWENT;	
			IBM TDB	
-	5553853	high enar2 density near3 plasma or HDP	USPAT;	2003/11/14
			US-PGPUB;	16:03
]			EPO; JPO;	
			DERWENT; IBM TDB	
-	12061	high near2 density near3 plasma or HDP	USPAT;	2003/11/14
		J	US-PGPUB;	16:05
			EPO; JPO;	
			DERWENT;	
ļ	344		IBM_TDB	
-	702	(high near2 density near3 plasma or HDP)	USPAT;	2003/11/14
	! 	same (deposit\$ or etch\$) same advantag\$	US-PGPUB;	16:04
			EPO; JPO; DERWENT;	
			IBM TDB	
[-	489	(high near2 density near3 plasma or HDP)	USPAT;	2003/11/14
	İ	same (deposit\$) same advantag\$	US-PGPUB;	16:04
			EPO; JPO;	
			DERWENT;	
	3	((high pear) dengity many) -1	IBM_TDB	2002/11/14
	3	((high near2 density near3 plasma or HDP) same (deposit\$) same advantag\$) and	USPAT;	2003/11/14
		117/\$.ccls.	US-PGPUB; EPO; JPO;	10:04
			DERWENT;	ļ
			IBM TDB	ĺ
-	9406	high adj density adj plasma or HDP	USPAT;	2003/11/14
			US-PGPUB;	16:05
			EPO; JPO;	
			DERWENT;	
	 l		IBM TDB	

_	162	(high adj density adj	plasma or HDP)	USPAT;	2003/11/14
		near10 advantag\$ same	(deposit\$)	US-PGPUB;	16:07
ļ				EPO; JPO;	
	İ			DERWENT;	
-				IBM TDB	
_	73	(high adj density adj	plasma or HDP)	USPĀT;	2003/11/17
		near10 advantag\$ same	(deposit\$ and	US-PGPUB;	09:35
		etch\$)	·	EPO; JPO;	
	[•		DERWENT;	
				IBM TDB	